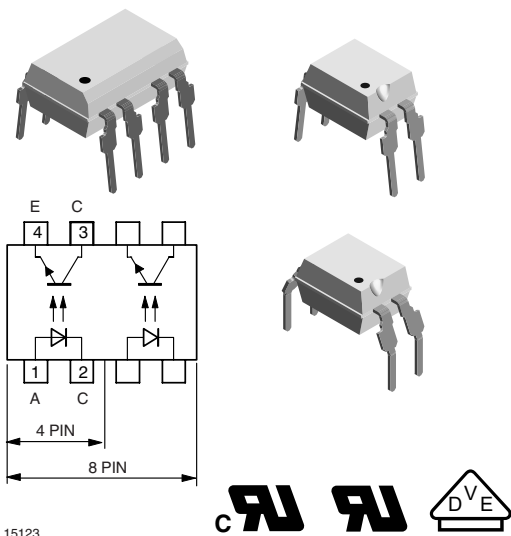


Optocoupler, Phototransistor Output (Single, Dual Channel)



15123



DESCRIPTION

The TCET1200/TCET2200 consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 4-pin (single channel) or 8-pin plastic dual inline package.

AGENCY APPROVALS

- UL1577, file no. E76222 system code U, double protection
- CSA 22.2 bulletin 5A, double protection
- BSI IEC 60950 IEC 60065
- DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 pending
- FIMKO

FEATURES

- Extra low coupling capacity - typical 0.2 pF
- High common mode rejection
- CTR offered in 5 groups
- Low temperature coefficient of CTR
- Available in single or dual channel
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

APPLICATIONS

- Switch-mode power supplies
- Line receiver
- Computer peripheral interface
- Microprocessor system interface
- Reinforced isolation provides circuit protection against electrical shock (safety class II)
- Circuits for safe protective separation against electrical shock according to safety class II (reinforced isolation):
 - for appl. class I - IV at mains voltage ≤ 300 V
 - for appl. class I - III at mains voltage ≤ 600 V according to DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 pending.

VDE STANDARDS

These couplers perform safety functions according to the following equipment standards:

- **DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 pending**
Optocoupler for electrical safety requirements
- **IEC 60950/EN 60950**
Office machines (applied for reinforced isolation for mains voltage ≤ 400 V_{RMS})
- **VDE 0804**
Telecommunication apparatus and data processing
- **IEC 60065**
Safety for mains-operated electronic and related household apparatus

TCET1200/TCET1200G/TCET2200

Vishay Semiconductors

Optocoupler, Phototransistor Output
(Single, Dual Channel)



ORDER INFORMATION	
PART	REMARKS
TCET1200	CTR 50 to 600 %, DIP-4
TCET1201	CTR 40 to 80 %, DIP-4
TCET2200	CTR 50 to 600 %, DIP-8
TCET1202	CTR 63 to 125 %, DIP-4
TCET1203	CTR 100 to 200 %, DIP-4
TCET1204	CTR 160 to 320 %, DIP-4
TCET1200G	CTR 50 to 600 %, DIP-4
TCET1201G	CTR 40 to 80 %, DIP-4
TCET1202G	CTR 63 to 125 %, DIP-4
TCET1203G	CTR 100 to 200 %, DIP-4
TCET1204G	CTR 160 to 320 %, DIP-4

Note

G = leadform 10.16 mm; G is not marked on the body.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10 \mu s$	I_{FSM}	1.5	A
Power dissipation		P_{diss}	100	mW
Junction temperature		T_j	125	°C
OUTPUT				
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10 ms$	I_{CM}	100	mA
Power dissipation		P_{diss}	150	mW
Junction temperature		T_j	125	°C
COUPLER				
Isolation test voltage (RMS)		V_{ISO}	5000	V_{RMS}
Total power dissipation		P_{tot}	250	mW
Operating ambient temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 55 to + 125	°C
Soldering temperature	2 mm from case, $t \leq 10 s$	T_{sld}	260	°C

Note

$T_{amb} = 25 \text{ }^{\circ}\text{C}$, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.



TCET1200/TCET1200G/TCET2200

Optocoupler, Phototransistor Output
(Single, Dual Channel)

Vishay Semiconductors

ELECTRICAL CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.25	1.6	V
Junction capacitance	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$	C_j		50		pF
OUTPUT						
Collector emitter voltage	$I_C = 1 \text{ mA}$	V_{CEO}	70			V
Emitter collector voltage	$I_E = 100 \mu\text{A}$	V_{ECO}	7			V
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}$, $I_F = 0 \text{ A}$, $E = 0$	I_{CEO}		10	100	nA
COUPLER						
Collector emitter saturation voltage	$I_F = 10 \text{ mA}$, $I_C = 1 \text{ mA}$	V_{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5 \text{ V}$, $I_F = 10 \text{ mA}$, $R_L = 100 \Omega$	f_c		110		kHz
Coupling capacitance	$f = 1 \text{ MHz}$	C_k		0.3		pF

Note

$T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified.

Minimum and maximum values were tested requirements. Typical values are characteristics of the device and are the result of engineering evaluations. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$V_{CE} = 5 \text{ V}$, $I_F = 5 \text{ mA}$	TCET1200	CTR	50		600	%
		TCET1200G	CTR				%
	$V_{CE} = 5 \text{ V}$, $I_F = 10 \text{ mA}$	TCET1201	CTR	40		80	%
		TCET1201G	CTR				%
		TCET1202	CTR	63		125	%
		TCET1202G	CTR				%
		TCET1203	CTR	100		200	%
		TCET1203G	CTR				%
		TCET1204	CTR	160		320	%
		TCET1204G	CTR				%
	$V_{CE} = 5 \text{ V}$, $I_F = 5 \text{ mA}$	TCET2200	CTR	50		600	%

MAXIMUM SAFETY RATINGS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward current		I_F			130	mA
OUTPUT						
Power dissipation		P_{diss}			265	mW
COUPLER						
Rated impulse voltage		V_{IOTM}			8	kV
Safety temperature		T_{si}			150	$^\circ\text{C}$

Note

According to DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 pending (see figure 1). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Partial discharge test voltage - routine test	100 %, $t_{\text{test}} = 1 \text{ s}$	V_{pd}	1.6			kV
Partial discharge test voltage - lot test (sample test)	$t_{\text{Tr}} = 60 \text{ s}$, $t_{\text{test}} = 10 \text{ s}$, (see figure 2)	V_{IOTM}	8			kV
		V_{pd}	1.3			kV
		R_{IO}	10^{12}			Ω
Insulation resistance	$V_{\text{IO}} = 500 \text{ V}$	R_{IO}	10^{11}			Ω
	$V_{\text{IO}} = 500 \text{ V}$, $T_{\text{amb}} = 100^\circ\text{C}$	R_{IO}	10^{11}			Ω
	$V_{\text{IO}} = 500 \text{ V}$, $T_{\text{amb}} = 150^\circ\text{C}$ (construction test only)	R_{IO}	10^9			Ω

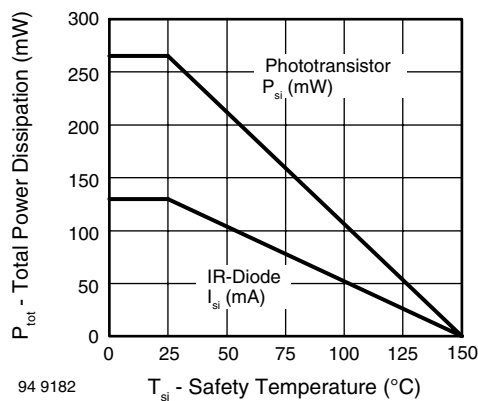


Fig. 1 - Derating Diagram

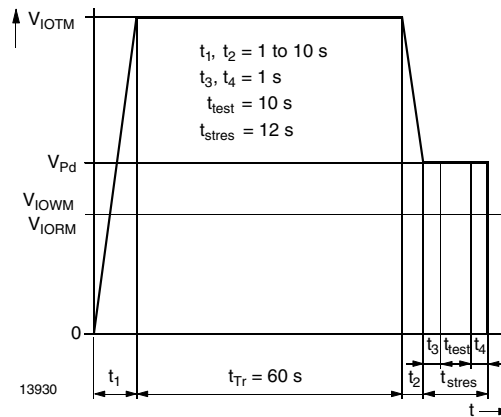


Fig. 2 - Test Pulse Diagram for Sample Test according to DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-; IEC60747

SWITCHING CHARACTERISTICS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Delay time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_d		3.0		μs
Rise time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_r		3.0		μs
Fall time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_f		4.7		μs
Storage time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_s		0.3		μs
Turn-on time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_{on}		6.0		μs
Turn-off time	$V_S = 5 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$, (see figure 3)	t_{off}		5.0		μs
Turn-on time	$V_S = 5 \text{ V}$, $I_F = 10 \text{ mA}$, $R_L = 1 \text{ k}\Omega$, (see figure 4)	t_{on}		9.0		μs
Turn-off time	$V_S = 5 \text{ V}$, $I_F = 10 \text{ mA}$, $R_L = 1 \text{ k}\Omega$, (see figure 4)	t_{off}		10		μs

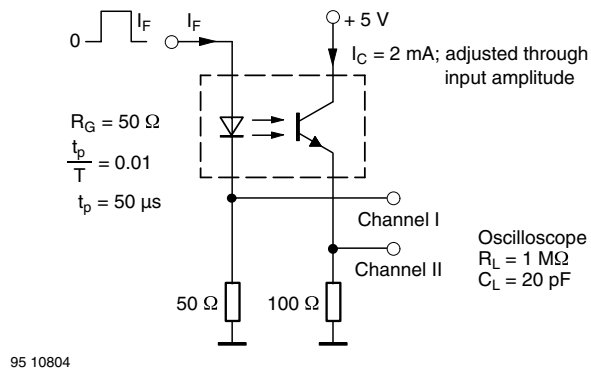


Fig. 3 - Test Circuit, Non-Saturated Operation

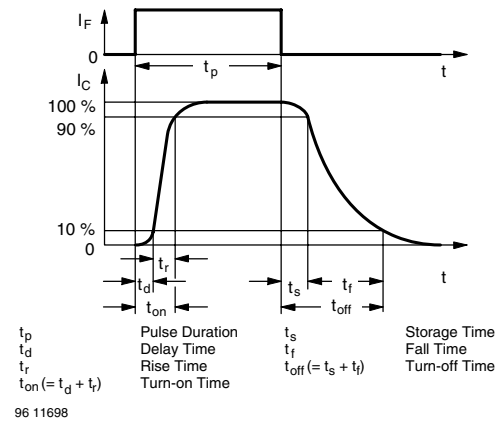


Fig. 5 - Switching Times

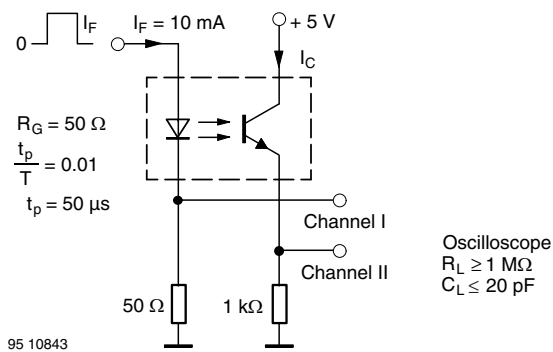


Fig. 4 - Test Circuit, Saturated Operation

TYPICAL CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

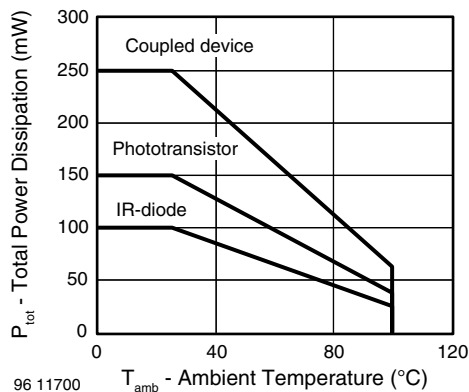


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

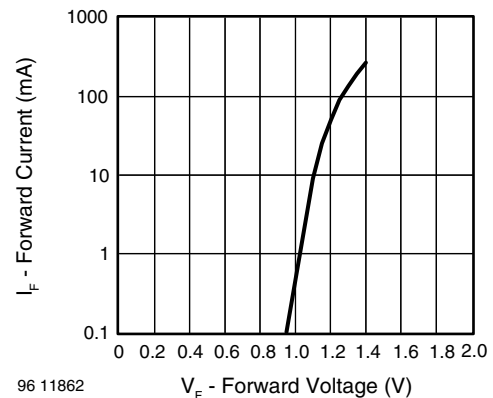


Fig. 7 - Forward Current vs. Forward Voltage

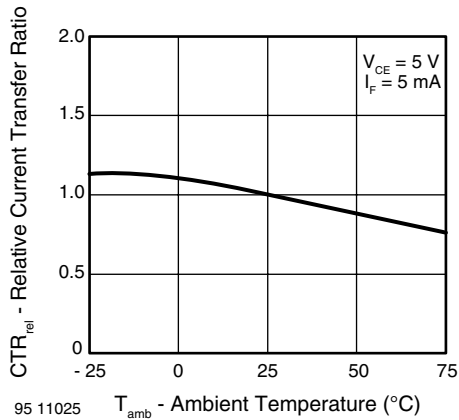


Fig. 8 - Relative Current Transfer Ratio vs. Ambient Temperature

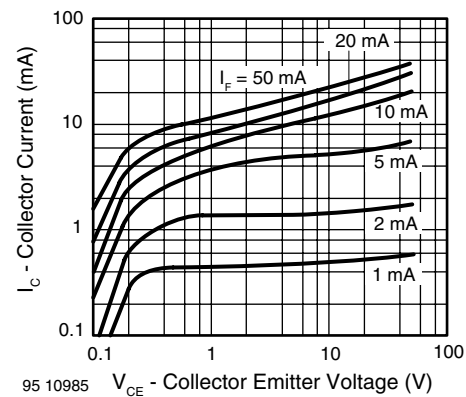


Fig. 11 - Collector Current vs. Collector Emitter Voltage

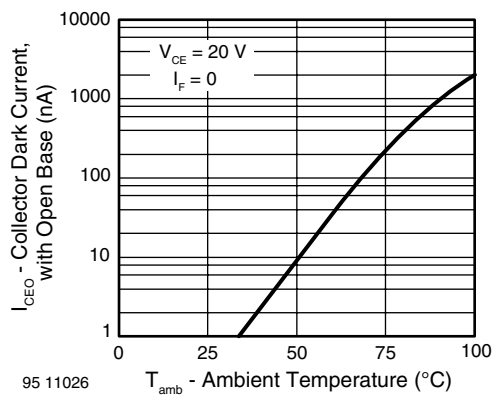


Fig. 9 - Collector Dark Current vs. Ambient Temperature

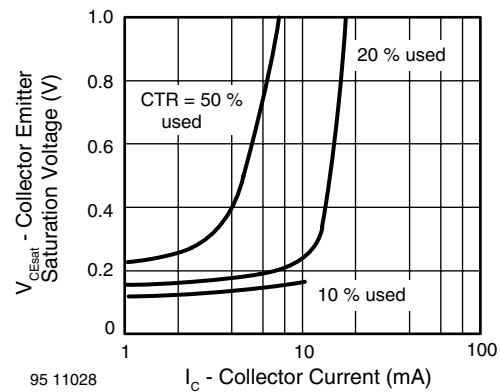


Fig. 12 - Collector Emitter Saturation Voltage vs. Collector Current

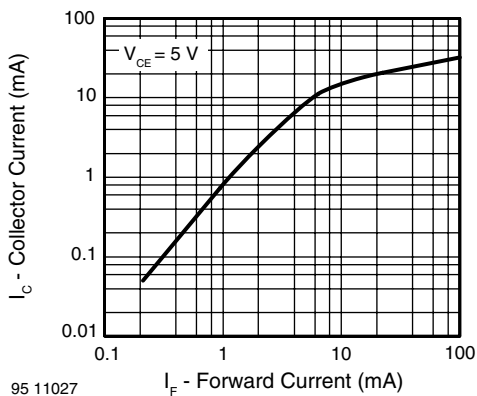


Fig. 10 - Collector Current vs. Forward Current

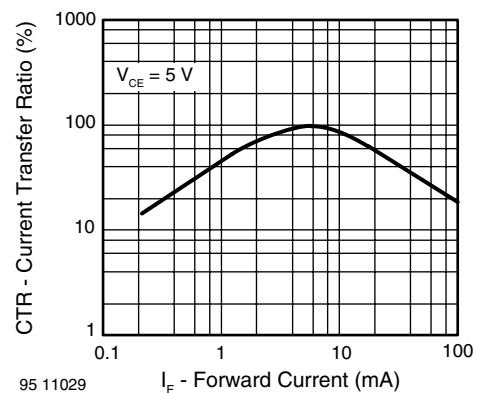


Fig. 13 - Current Transfer Ratio vs. Forward Current

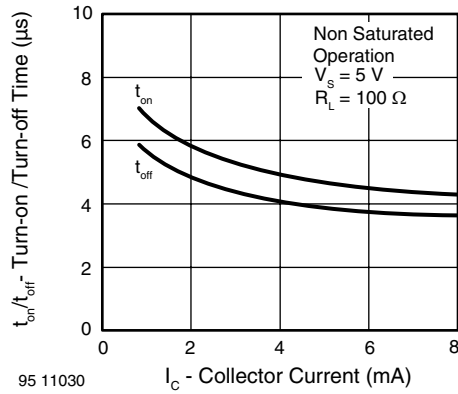


Fig. 14 - Turn-on/off Time vs. Collector Current

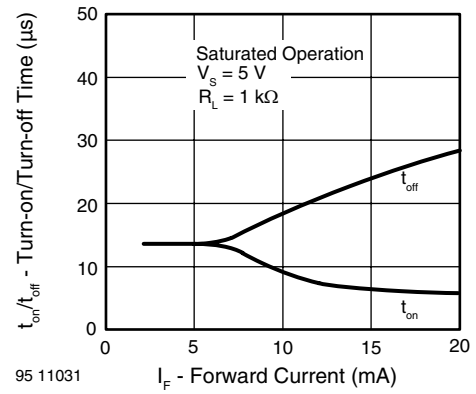
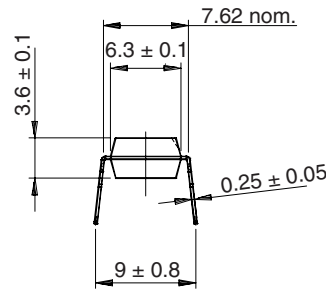
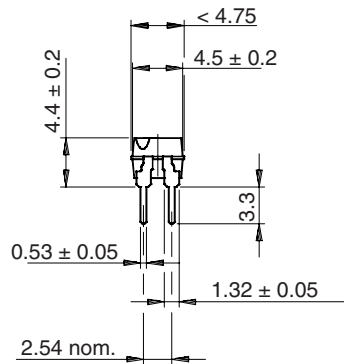


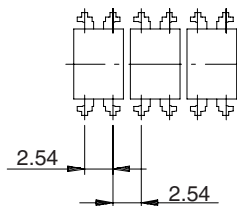
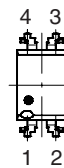
Fig. 15 - Turn-on/off Time vs. Forward Current

PACKAGE DIMENSIONS in millimeters

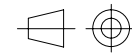


E. g.:
Special Features: Endstackable
to 2.54 mm (0.100") Spacing

Weight: ca. 0.25 g
Creepage Distance: > 6 mm
Air Path: > 6 mm
after Mounting on PC Board

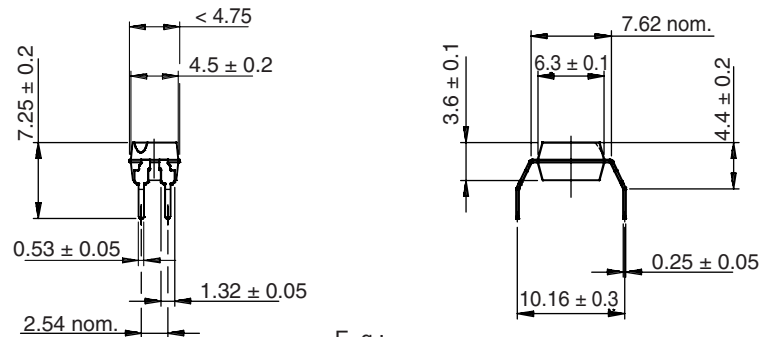


Drawing-No.: 6.544-5302.03-4
Issue: 5; 20.03.02

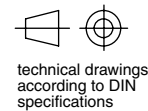
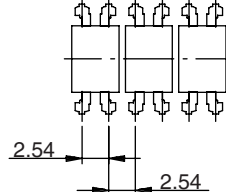
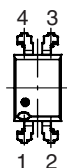


technical drawings
according to DIN
specifications

14789



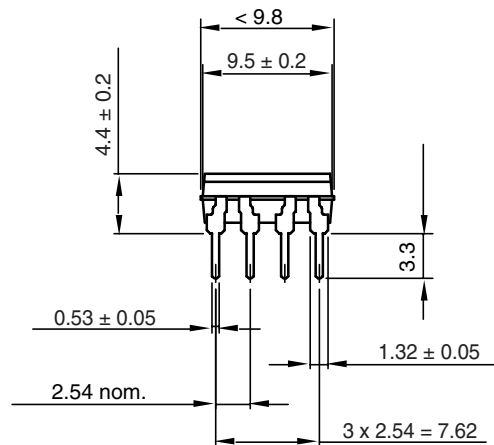
E. g.:
Special Features: Endstackable
to 2.54 mm (0.100") Spacing



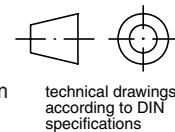
Weight: ca. 0.25 g
Creepage Distance: > 8 mm
Air Path: > 8 mm
after Mounting on PC Board

Drawing-No.: 6.544-5303.03-4
Issue: 4; 20.03.02

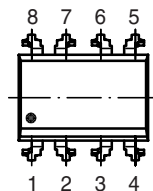
14792



Weight: ca. 0.55 g
Creepage Distance: > 6 mm
Air Path: > 6 mm
after Mounting on PC Board



Drawing-No.: 6.544-5302.02-4
Issue: 4; 02.06.99



14784

**OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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